

Silicon NPN Power Transistors

2SC1162

DESCRIPTION

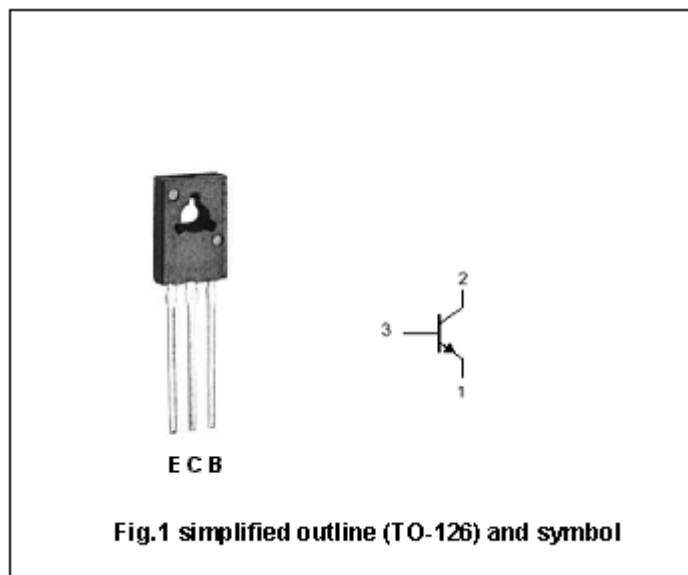
- With TO-126 package
- Complement to type 2SA715

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute Maximun Ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	35	V
V_{CEO}	Collector-emitter voltage	Open base	35	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		2.5	A
I_{CM}	Collector current-peak		3	A
P_C	Collector power dissipation	$T_a=25^{\circ}\text{C}$	0.75	W
		$T_C=25^{\circ}\text{C}$	10	
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA I _B =0	35			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	35			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2.0A ; I _B =0.2A(Pulse test)			1.0	V
V _{BE}	Base-emitter on voltage	I _C =1.5A ; V _{CE} =2V(Pulse test)			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =35V ; I _E =0			20	μA
I _{EBO}	Emitter cut-off current	V _{EB} =3V ; I _C =0			1	μA
h _{FE-1}	DC current gain	I _C =0.5A ; V _{CE} =2V	60		320	
h _{FE-2}	DC current gain	I _C =1.5A ; V _{CE} =2V(Pulse test)	20			
f _T	Transition frequency	I _C =0.2A ; V _{CE} =2V(Pulse test)		180		MHz

◆ h_{FE-1} Classifications

B	C	D
60-120	100-200	160-320

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PACKAGE OUTLINE

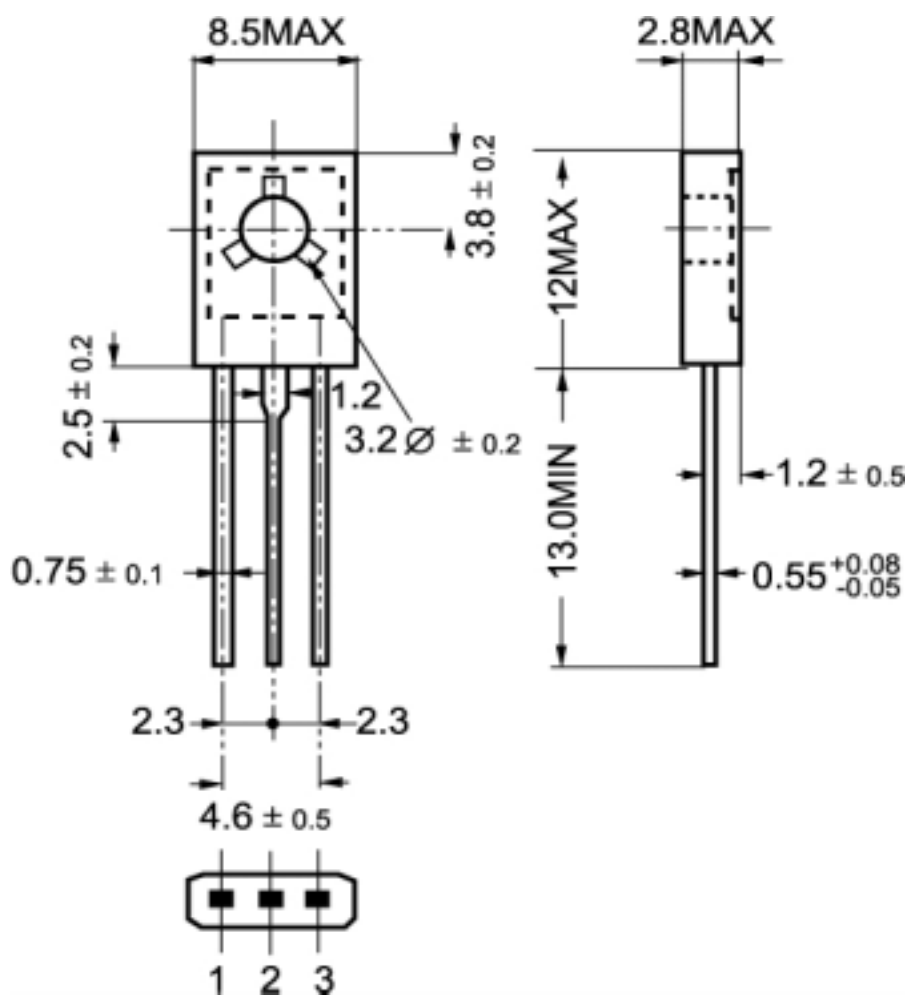


Fig.2 Outline dimensions

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